

## Description

MOSFET Product Summary				
V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)		
1700	45	72		

# S D G

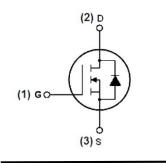
TO-247-3L (Top View)

#### **Feature**

- High Speed Switching with Low Capacitances
- ➤ High Blocking Voltage with Low RDS(on)
- > Avalanche Ruggednes

### **Applications**

- Solar Inverters
- > Switch Mode Power Supplies
- ➤ High Voltage DC-DC Converters
- Batterry Chargers



Schematic diagram

# Absolute maximum rating@25°C

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V <sub>DS</sub>	1700	V
Gate-Source Voltage		$V_{GS}$	-10/+25	V
Continuous Drain Current	ntinuous Drain Current  T <sub>C</sub> =25°C  72	72	_	
Continuous Drain Current	T <sub>C</sub> =100°C	l <sub>D</sub>	50	Α
Pulsed drain current (TC = 25°C, tp limited by Tjmax)		I <sub>D pulse</sub>	160	Α
Power dissipation ( $T_C = 25^{\circ}C$ )		P <sub>tot</sub>	338	W
Operating Junction Temperature		T <sub>J</sub>	-55 to +150	°C
Storage Temperature		T <sub>STG</sub>	-55 to +150	°C

#### Thermal Resistance

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	0.37	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	40	°C/W

# Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Statistic Characteristics	•					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS} = 0V, I_{D} = 100 \mu A$	1700	-	-	V
Zero Gate Voltage Drain Current @V <sub>DS</sub> =		T <sub>C</sub> =25°C	-	1	100	
1700V,V <sub>GS</sub> = 0V	I <sub>DSS</sub>	T <sub>C</sub> =175°C	-	10	-	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS} = 20V,$ $V_{DS} = 0V$	ı	10	600	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 18 \text{mA}$	2.0	2.6	4.0	V
Drain-Source On-State Resistance @V <sub>GS</sub> =		T <sub>J</sub> =25°C	-	27	45	
20V,I <sub>D</sub> = 50A	R <sub>DS(ON)</sub>	T <sub>J</sub> =150°C	-	45	-	mΩ
Dynamic Characteristics						
Input Capacitance	C <sub>lss</sub>		-	5070	-	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 1000V, f=1MHz, V_{GS} = 0V$	-	240	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	- 50		50	-	
Transconductance	g <sub>fs</sub>	$V_{DS} = 20V, I_{D} = 20A$	1	26.8	-	S
Turn-On Energy (Body Diode)	E <sub>on</sub>	V <sub>GS</sub> =-1.5/20V,	-	5.33	-	m
Turn-Off Energy (Body Diode)	E <sub>off</sub>	$I_D = 50A, V_{DS} = 1200V,$ $R_g = 15\Omega$ - 4.0		4.07	-	mJ
Turn-on Delay Time	t <sub>d(on)</sub>		-	18	-	
Turn-on Rise Time	t <sub>r</sub>	I <sub>D</sub> =50A, V <sub>DS</sub> =1200V,	-	64	-	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		210	-	ns
Turn-Off Fall Time	t <sub>f</sub>	Timing relative to V <sub>DS</sub>	-	84	-	
Total Gate Charge	Qg		-	185	-	
Gate-Source Charge	$Q_{gs}$	V <sub>GS</sub> =-5/+20V, V <sub>DS</sub> =1200V, I <sub>D</sub> =50A	-	45	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>DS</sub> =1200V, I <sub>D</sub> =50A - 55		-		
Gate Resistance	$R_{G}$	$V_{GS}$ =0V, $V_{DS}$ =0V, $f$ =1MHz	-	3.5	-	Ω
Reverse Diode Characteristics						
Redy Diede Conyord Voltage		$V_{GS}$ =-5V, $I_{SD}$ =25A, $T_{J}$ =25°C	-	5.4	-	V
Body Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =-5V,I <sub>SD</sub> =25A, T <sub>J</sub> =150°C	-	4.8	-	v
Body Diode Reverse Recovery Time	t <sub>rr</sub>	$V_{DS}$ =1200V, $V_{GS}$ = -5V,	-	96	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	l <sub>SD</sub> =50A, di/dt=1053A/μs	-	915	-	nC

# **Typical Characteristics**

Fig 1. Output Characteristic (T<sub>J</sub>=25°C)

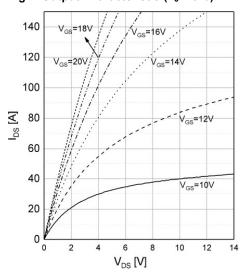


Fig 3: Transfer Characteristic ( $V_{DS}$ =20V)

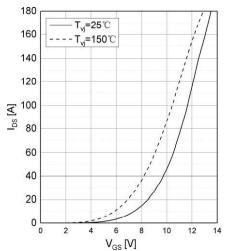


Fig 7: Body-diode Characteristic (T<sub>J</sub>=150°C)

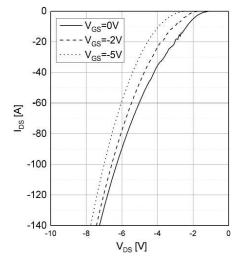


Fig 2. Output Characteristic (T<sub>J</sub>=150°C)

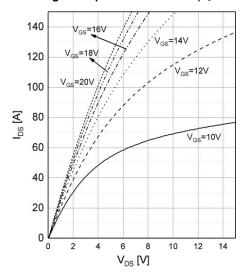
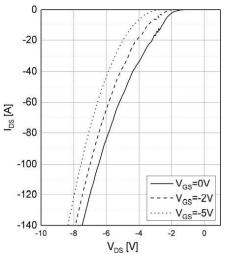
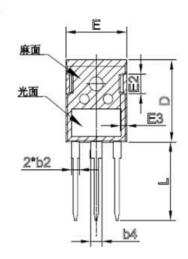


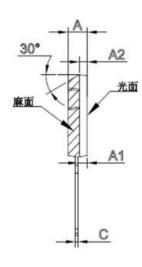
Fig 6: Body-diode Characteristic (TJ=25°C)

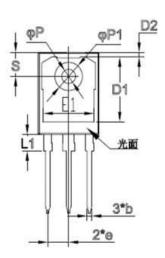


# Product dimension (TO-247-3L)

Unit:mm







	Min	Nom	Max		Min	Nom	Max
Α	4.70	5.00	5.20	E1	13.06	13.26	13.5
A1	2.30	,	2.50	E2	4.90	5.00	5.10
A2	1.90	2.00	2.10	E3	1.50	1.60	1.70
b	1.10	1.20	1.30	0	5.34	5.44	5.54
b2		2.00		L	19.80	20.00	20.3
<b>b4</b>		3.00		L1		4.17	4.50
С	0.5	0.6	0.7	Р	3.50	3.60	3.70
D	20.8	20.95	21.1	P1	7.00	7.19	7.40
D1		16.55		s	6.04	6.15	6.3
D2	0.95	1.17	1.35				
E	15.48	15.88	16.28				

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